IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

founded by NXP

MAC97A6

4Q Triac

1 May 2015 **Product data sheet**

1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- General purpose low power phase control
- General purpose low power switching
- Solid-state relay

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	400	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5		-	-	8	A
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 50$ °C; Fig. 1; Fig. 2; Fig. 3		-	-	0.6	A
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	1	5	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	2	5	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	2	5	mA

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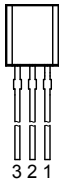
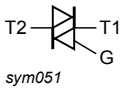
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	4	7	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 TO-92 (SOT54)	 sym051
2	G	gate		
3	T1	main terminal 1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
MAC97A6	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	400	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 50$ °C; Fig. 1; Fig. 2; Fig. 3		-	0.6	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5		-	8	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		-	8.8	A
I^2t	I2t for fusing	$t_p = 10$ ms; SIN		-	0.32	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 10$ mA; T2+ G+		-	50	A/µs
		$I_G = 10$ mA; T2+ G-		-	50	A/µs
		$I_G = 14$ mA; T2- G+		-	10	A/µs
		$I_G = 10$ mA; T2- G-		-	50	A/µs
I_{GM}	peak gate current	t = 20 microsecs (max)		-	1	A
P_{GM}	peak gate power			-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period; T(lead) ≤ 80 °C; t = 2 microseconds (max)		-	0.1	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	125	°C

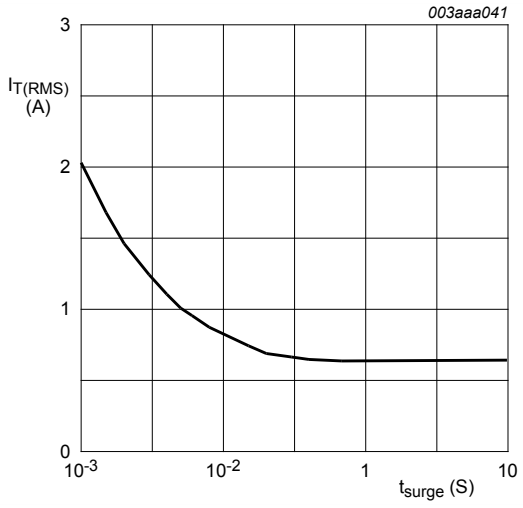

Fig. 1. RMS on-state current as a function of surge duration; maximum values

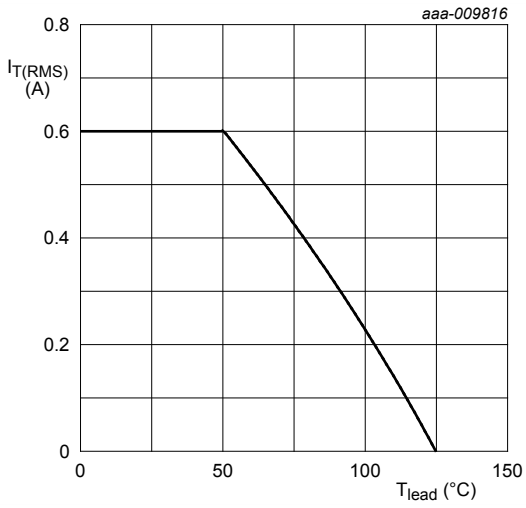

Fig. 2. RMS on-state current as a function of lead temperature; maximum values

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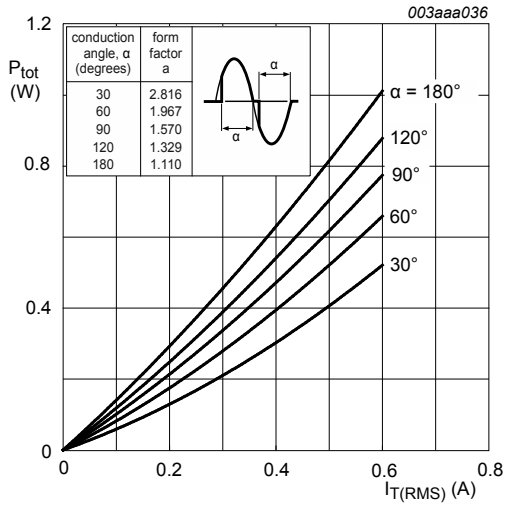
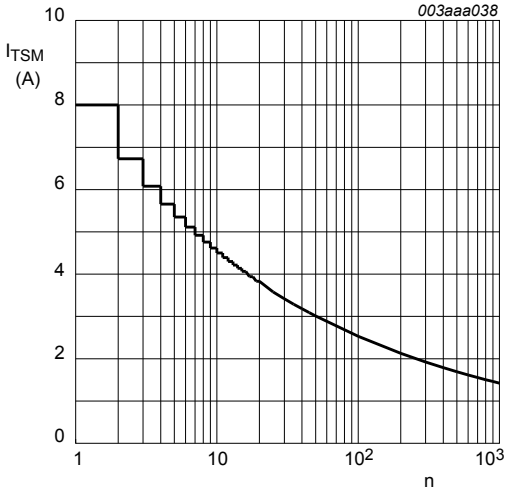


α = conduction angle

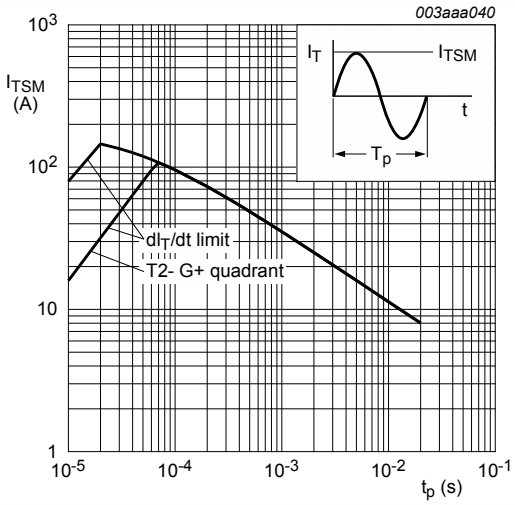
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 20 ms

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6		-	-	60	K/W
		half cycle		-	-	80	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm		-	150	-	K/W

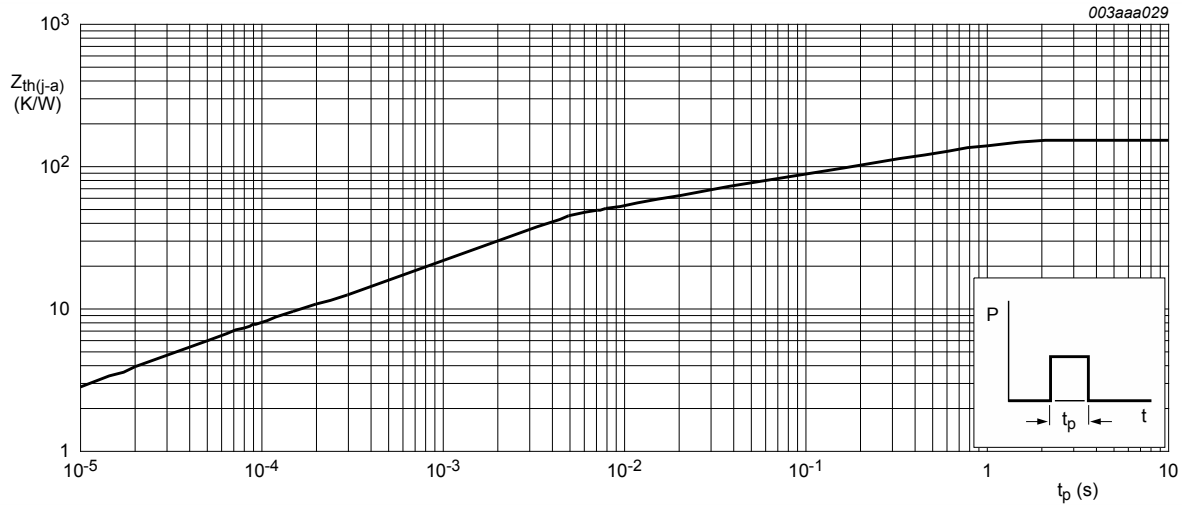

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse width

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	1	5	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	2	5	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	2	5	mA
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	4	7	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C		-	1	10	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	5	10	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	1	10	mA
		V_D = 12 V; I_G = 0.1 A; T2- G+; T_j = 25 °C; Fig. 8		-	2	10	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	1	10	mA
V_T	on-state voltage	I_T = 0.85 A; T_j = 25 °C; Fig. 10		-	1.4	1.9	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.9	1.5	V
		V_D = 400 V; I_T = 0.1 A; T_j = 110 °C; Fig. 11		0.1	0.7	-	V
I_D	off-state current	V_D = 400 V; T_j = 110 °C		-	3	100	µA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12		30	45	-	V/µs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 50 °C; dI_{com}/dt = 0.3 A/ms; I_T = 0.84 A; gate open circuit		-	5	-	V/µs
t_{gt}	gate-controlled turn-on time	I_{TM} = 1 A; V_D = 400 V; I_G = 25 mA; dI_G/dt = 5 A/µs		-	2	-	µs

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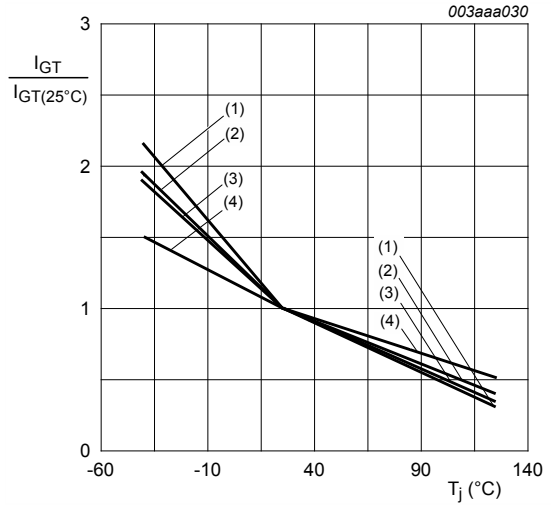


(1) T2- G+
(2) T2- G-
(3) T2+ G-
(4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

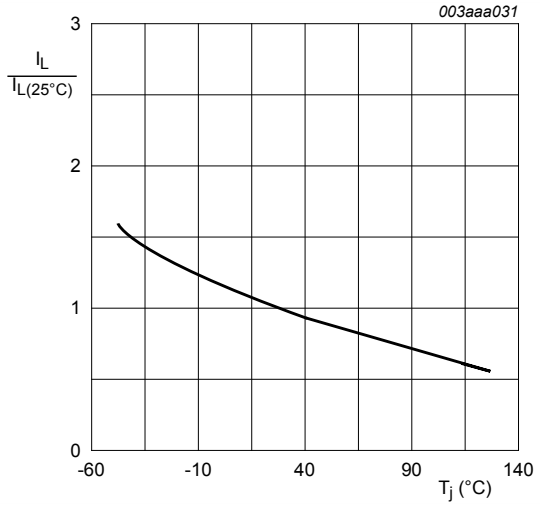


Fig. 8. Normalized latching current as a function of junction temperature

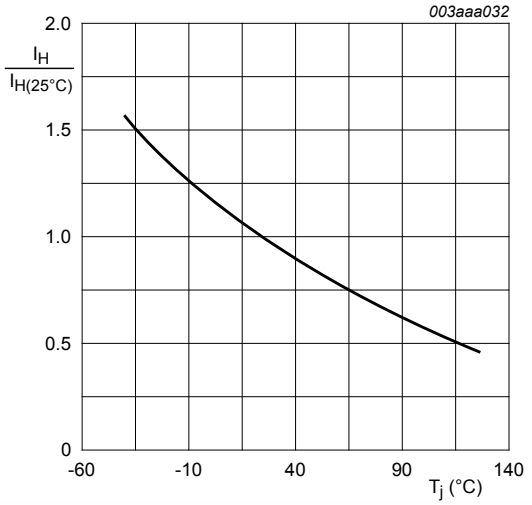
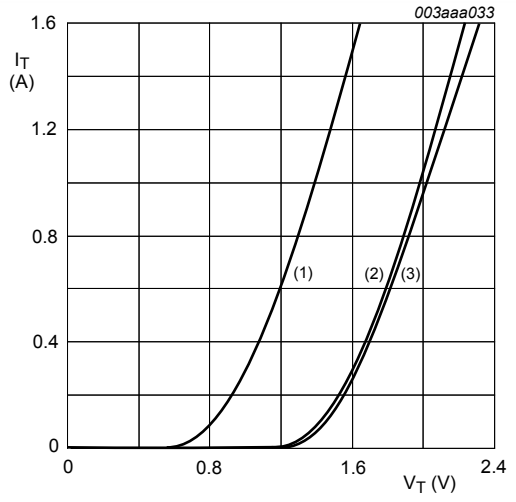


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.45 V; R_s = 0.1875 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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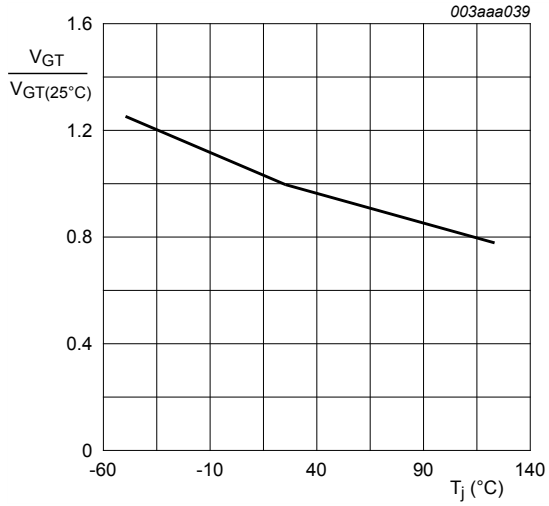

Fig. 11. Normalized gate trigger voltage as a function of junction temperature

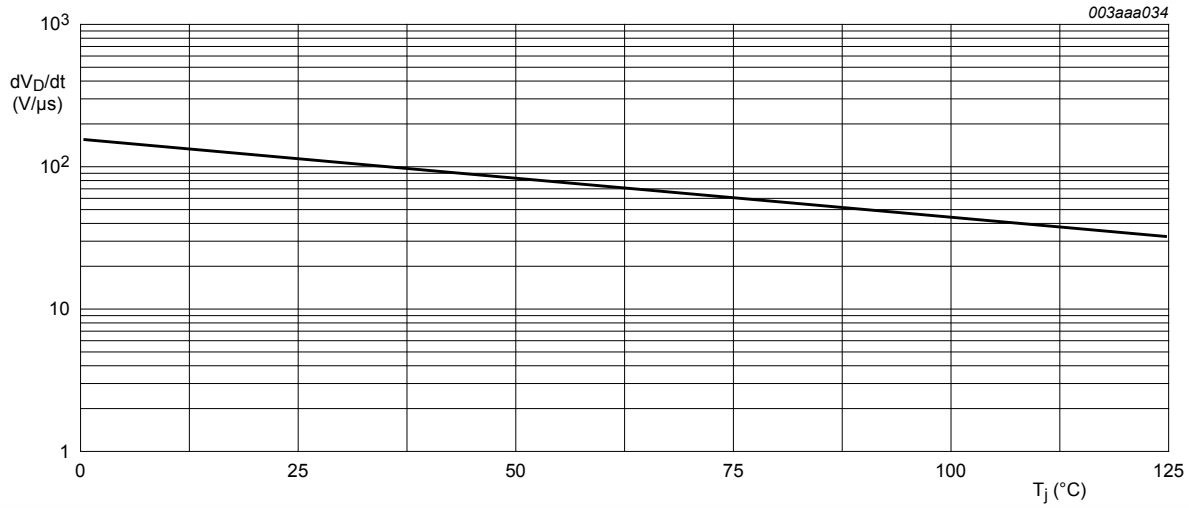

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

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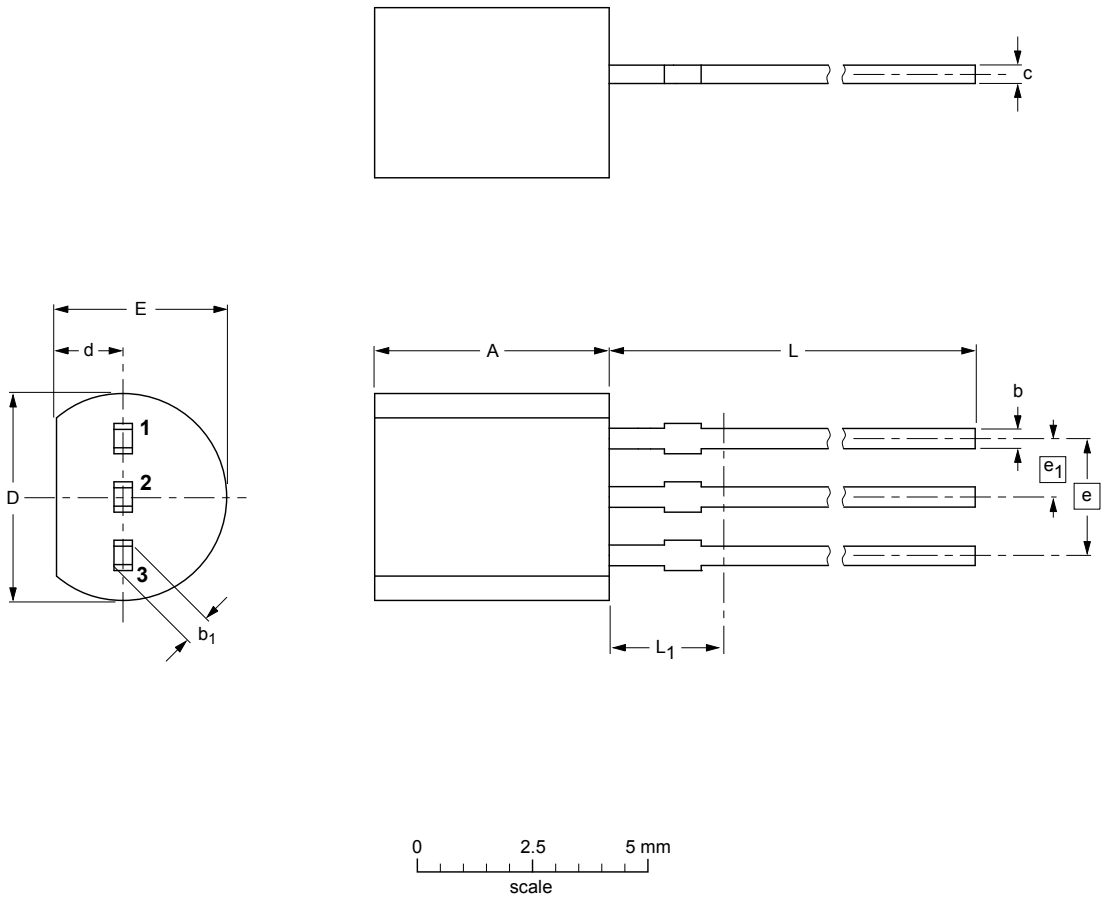
10. Package outline

Plastic single-ended leaded (through hole) package; 3 leads **SOT54**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b_1	c	D	d	E	e	e_1	L	L_1 (1) max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			~~04-06-28~~ 04-11-16

Fig. 13. Package outline TO-92 (SOT54)

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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 1 May 2015